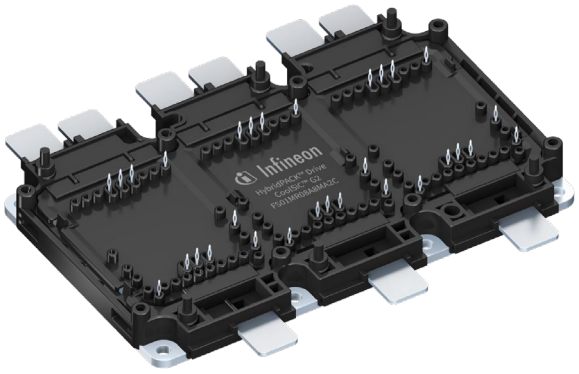
Final datasheet
基于 SiC MOSFET 的HybridPACK™ Drive G2模块

特性



- 电气特性
  - V_{DSS} = 750V
  - $I_{D,nom}$ = 620 A
  - 新型半导体材料—碳化硅
  - 低 $R_{DS,on}$
  - 低开关损耗
  - 低 Q_g和 C_{rss}
  - 低电感设计
  - $T_{vj,op}$ = 175°C
  - 短时延长工作温度 $T_{vj,op}$ = 200 °C
- 机械特性
  - 4.25 kV 直流电压 1 秒绝缘
  - 高爬电距离和电气间隙
  - 紧凑型设计
  - 高功率密度
  - 直冷式 PinFin 底板
  - 高性能Si_3N_4陶瓷
  - PCB 和冷却器组装用导向元件
  - 集成温度传感二极管
  - PressFIT 压接技术
  - 符合 RoHS 标准，无铅
  - UL 94 V0 模块框架

Green
Lead-free
RoHS

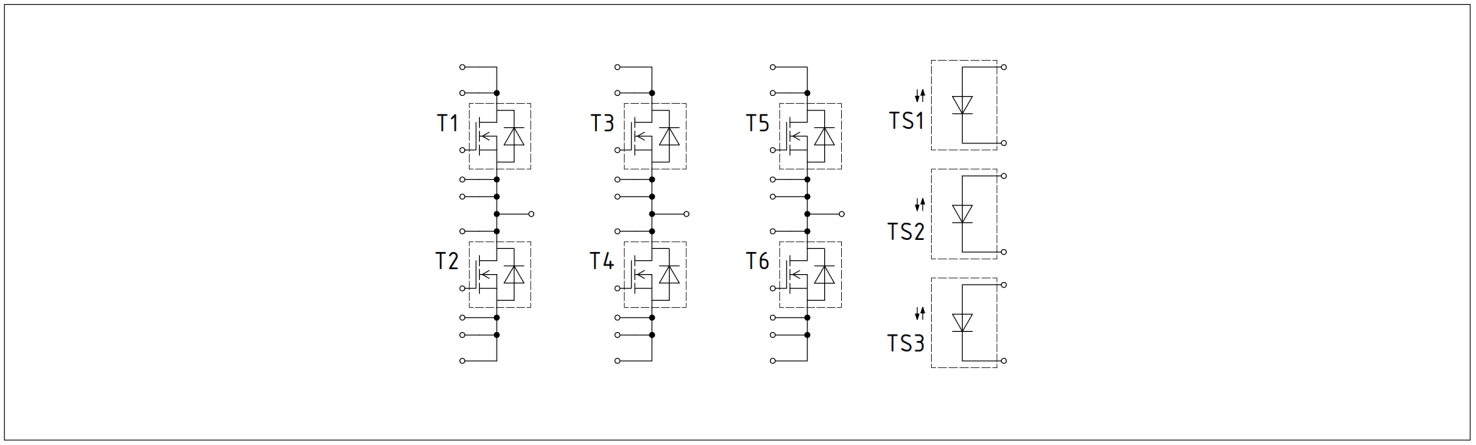
潜在应用

- 汽车应用
- （混合动力）电动汽车 (H)EV
- 电机驱动
- 商用、建筑和农用车辆 (CAV)

产品验证

- 符合 AQG 324 标准，发布号：03.1/2021

描述



本数据手册的原文使用英文撰写。为方便起见，英飞凌提供了译文；由于翻译过程中可能使用了自动化工具，英飞凌不保证译文的准确性。为确认准确性，请务必访问 infineon.com 参考最新的英文版本（控制文档）。

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1 封装

表1 绝缘配合

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, f = 0 Hz, t = 1 sec	4.25	kV
Material of module baseplate			Cu+Ni[1)]	
Internal isolation		basic insulation (class 1, IEC 61140)	Si_3N_4	
Creepage distance	d_{creep}	terminal to heatsink	10.6	mm
Creepage distance	d_{creep}	terminal to terminal	10.6	mm
Clearance	d_{clear}	terminal to heatsink	4.5	mm
Clearance	d_{clear}	terminal to terminal	4.5	mm
Comparative tracking index	*CTI*		> 175	

1) 镀镍铜底板

表 2 最大额定值

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Maximum RMS module terminal current	$I_{t,rms}$	T_{Ct} = 125 °C		900		A
Heat-staking dome temperature[1)]	T_{HS}	$t_{staking}$ < 10s			280	°C

1) 热熔组装参考应用笔记 AN-G2-ASSEMBLY 。

表3 特征值

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Pressure drop in cooling circuit	Δp	50% water / 50% ethylene glycol, $\Delta V/\Delta t$ = 10 dm^3/min, T_f = 60 °C		76[1)]		mbar
Maximum pressure in cooling circuit	p	$T_{baseplate}$ < 40 °C (relative pressure)			3.0	bar
		$T_{baseplate}$ ≥ 40 °C (relative pressure)			2.5	
Stray inductance module	$L_{s,DS}$			8.0		nH
Module lead resistance, terminals - chip	$R_{DD'+SS'}$	T_f = 25 °C, per switch		0.64		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting torque for module mounting[2)]	M	Screw M4 baseplate to heatsink	1.8	2.0	2.2	Nm
		Screw EJOT Delta PCB to frame	0.45	0.5	0.55	
Weight	G			760		g

1) 冷却器设计和流动方向参考应用笔记 AN-G2-ASSEMBLY 。

2) 螺钉类型和扭矩参考应用笔记 AN-G2-ASSEMBLY。

2 MOSFET

表4 最大额定值

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}		continuous operation	750	V
			10h over life time	900	
DC drain current	$I_{D,nom}$	V_{GS} = 18 V, T_f = 65 °C	$T_{vj,max}$ = 175 °C	620	A
Pulsed drain current	$I_{D,pulse}$	verified by design, t_p limited by $T_{vj,max}$		1240	A
Gate-source voltage, max. static voltage	V_{GS}			-5/19	V
Gate-source voltage, max. transient voltage	V_{GS}	Duty Cycle < 1 % (first transient maximum peak)		-10/23	V

表 5 建议值

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{GS(on)}$		15...18	V
Off-state gate voltage	$V_{GS(off)}$		-5	V

表 6 特征值

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-resistance	$R_{DS,on}$	I_D = 620 A, V_{GS} = 18 V	T_{vj} = 25 °C		1.03	1.69	mΩ
			T_{vj} = 125 °C		1.45		
			T_{vj} = 175 °C		1.80		
			T_{vj} = 200 °C		2.00		
Drain-source on-resistance	$R_{DS,on}$	I_D = 620 A, V_{GS} = 15 V	T_{vj} = 25 °C		1.28	2.00	mΩ
			T_{vj} = 125 °C		1.65		
			T_{vj} = 175 °C		1.99		
			T_{vj} = 200 °C		2.21		
Gate threshold voltage	$V_{GS,th}$	I_D = 200 mA, V_{GS} = V_{DS}, (tested after 1ms pulse at V_{GS} = +20 V)	T_{vj} = 25 °C	3.20*1)*	3.90	4.55	V
Total gate charge	Q_G	V_{DS} = 470 V, V_{GS} = -5/18 V			1.50		µC
Internal gate resistor	$R_{G,int}$		T_{vj} = 25 °C		0.53		Ω
Input capacitance	C_{iss}	f = 1 MHz, V_{DS} = 470 V	T_{vj} = 25 °C		43		nF
Output capacitance	C_{oss}	f = 1 MHz, V_{DS} = 470 V	T_{vj} = 25 °C		2.85		nF

（表格续下页.....）

表6　　（续）特征值

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Reverse transfer capacitance	C_{rss}	f = 1 MHz, V_{DS} = 470 V	T_{vj} = 25 °C		0.25		nF
C_{oss} stored energy	E_{oss}	V_{DS} = 470 V	T_{vj} = 25 °C		1250		µJ
Drain-source leakage current	I_{DSX}	V_{GS} = -5 V, V_{DSS} = 750 V	T_{vj} = 25 °C			100	µA
Gate-source leakage current	I_{GSS}	V_{GS} = 20 V, V_{DS} = 0 V	T_{vj} = 25 °C			100	nA
Turn-on delay time, inductive load	$t_{d,on}$	I_D = 620 A, $R_{G,on}$ = 10.5 Ω, V_{GS} = -5/18 V, V_{DS} = 470 V	T_{vj} = 25 °C		128		ns
			T_{vj} = 125 °C		107		
			T_{vj} = 175 °C		99		
			T_{vj} = 200 °C		96		
Rise time (inductive load)	t_r	I_D = 620 A, $R_{G,on}$ = 10.5 Ω, V_{GS} = -5/18 V, V_{DS} = 470 V	T_{vj} = 25 °C		108		ns
			T_{vj} = 125 °C		103		
			T_{vj} = 175 °C		101		
			T_{vj} = 200 °C		99		
Turn-off delay time, inductive load	$t_{d,off}$	I_D = 620 A, $R_{G,off}$ = 4.2 Ω, V_{GS} = -5/18 V, V_{DS} = 470 V	T_{vj} = 25 °C		318		ns
			T_{vj} = 125 °C		339		
			T_{vj} = 175 °C		352		
			T_{vj} = 200 °C		359		
Fall time (inductive load)	t_f	I_D = 620 A, $R_{G,off}$ = 4.2 Ω, V_{GS} = -5/18 V, V_{DS} = 470 V	T_{vj} = 25 °C		53		ns
			T_{vj} = 125 °C		57		
			T_{vj} = 175 °C		58		
			T_{vj} = 200 °C		59		
Turn-on energy loss per pulse	E_{on}	I_D = 620 A, $R_{G,on}$ = 10.5 Ω, V_{GS} = -5/18 V, V_{DS} = 470 V, L_σ = 6.5 nH	T_{vj} = 25 °C, di/dt = 4.69 kA/µs		27.60		mJ
			T_{vj} = 125 °C, di/dt = 4.93 kA/µs		26.40		
			T_{vj} = 175 °C, di/dt = 5 kA/µs		26.30		
			T_{vj} = 200 °C, di/dt = 5 kA/µs		26.30		

（表格续下页……）

表6　　（续）特征值

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-off energy loss per pulse	E_{off}	I_D = 620 A, $R_{G,off}$ = 4.2 Ω, V_{GS} = -5/18 V, V_{DS} = 470 V, L_σ = 6.5 nH	T_{vj} = 25 °C, dv/dt = 6.05 kV/µs		22.90		mJ
			T_{vj} = 125 °C, dv/dt = 5.87 kV/µs		23.80		
			T_{vj} = 175 °C, dv/dt = 5.8 kV/µs		24.30		
			T_{vj} = 200 °C, dv/dt = 5.75 kV/µs		24.50		
Short circuit data	I_{SC}	V_{DD} = 470 V, V_{GS} = -5/18 V, $R_{G,on}$ = 10.5 Ω, $R_{G,off}$ = 4.2 Ω, V_{DSmax} = V_{DSS}-L_{sDS}·di/dt	t_{SC} = 1.2 µs, T_{vj} = 200 °C		10000		A
Short circuit data	I_{SC}	V_{DD} = 470 V, V_{GS} = -5/15 V, $R_{G,on}$ = 10.5 Ω, $R_{G,off}$ = 4.2 Ω, V_{DSmax} = V_{DSS}-L_{sDS}·di/dt	t_{SC} = 2 µs, T_{vj} = 200 °C		6500		A
Thermal resistance, junction to cooling fluid[2)]	$R_{th,j-f}$	50% water / 50% ethylene glycol, $\Delta V/\Delta t$ = 10 dm³/min, T_f = 60 °C			0.107		K/W
Variance of thermal resistance, junction to cooling fluid[2)]	$\sigma_{Rth,j-f}$	50% water / 50% ethylene glycol, $\Delta V/\Delta t$ = 10 dm³/min, T_f = 60 °C			0.0024		K/W
Temperature under switching conditions	$T_{vj,op}$		continuous operation	-40		175	°C
			extended operation			200[3)]	

1) 在工作时间为 0h。在逆变器工作期间，该值可能会较低，具体取决于生命周期内的 T_{vj}、$V_{GS(off)}$、(开关频率)f_{sw}。对于 $V_{GS,th}$ Min 的最终评估值取决于客户应用，请联系英飞凌销售以获得英飞凌必要的技术支持。

2) 冷却器设计和流动方向参考应用笔记 AN-G2-ASSEMBLY。EoL 标准见 AQG324，通过特性验证。

3) 有关限制，请参见 QPAC 文档。

3　体二极管（MOSFET）

表 7　　最大额定值

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}		continuous operation	750	V
			10h over life time	900	
DC body diode forward current	$I_{F,S}$	V_{GS} = -5 V, T_f = 65 °C	$T_{vj,max}$ = 175 °C	193	A

（表格续下页……）

表 7　　（续）最大额定值

Parameter	Symbol	Note or test condition	Values	Unit
Pulsed body diode current	$I_{F,S,pulse}$	verified by design, t_p limited by $T_{vj,max}$	1240	A

表 8　　特征值

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	$V_{F,SD}$	$I_{F,S}$ = 620 A, V_{GS} = -5 V	T_{vj} = 25 °C		4.64	6.73	V
			T_{vj} = 125 °C		4.25		
			T_{vj} = 175 °C		4.09		
			T_{vj} = 200 °C		4.04		
Peak reverse recovery current	I_{rrm}	$I_{F,S}$ = 620 A, V_{GS} = -5 V, $V_{R,DS}$ = 470 V	T_{vj} = 25 °C		117		A
			T_{vj} = 125 °C		133		
			T_{vj} = 175 °C		152		
			T_{vj} = 200 °C		162		
Recovered charge	Q_{rr}	$I_{F,S}$ = 620 A, V_{GS} = -5 V, $V_{R,DS}$ = 470 V	T_{vj} = 25 °C		2.20		µC
			T_{vj} = 125 °C		3.60		
			T_{vj} = 175 °C		5.00		
			T_{vj} = 200 °C		5.70		
Reverse recovery energy	E_{rec}	$I_{F,S}$ = 620 A, V_{GS} = -5 V, $V_{R,DS}$ = 470 V	T_{vj} = 25 °C, $-di/dt$ = 5.4 kA/µs		0.310		mJ
			T_{vj} = 125 °C, $-di/dt$ = 5.6 kA/µs		0.540		
			T_{vj} = 175 °C, $-di/dt$ = 5.7 kA/µs		0.770		
			T_{vj} = 200 °C, $-di/dt$ = 5.8 kA/µs		0.900		

4　温度传感器

表 9　　特征值

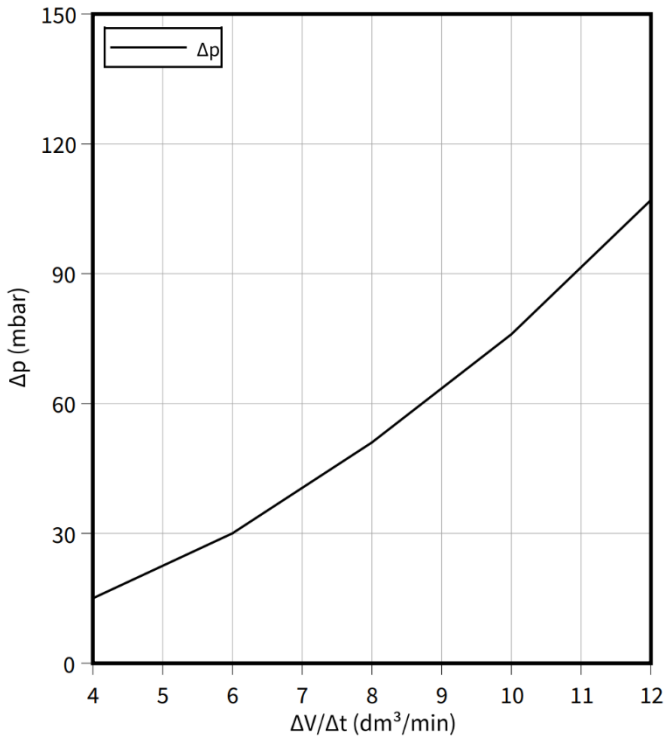
Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Transient sense current	I_{TS}					10	mA
Forward voltage	V_{TS}		I_{TS} = 0.2 mA, T_{vj} = 25 °C	2.574	2.624	2.674	V
			I_{TS} = 0.2 mA, T_{vj} = 85 °C	2.169	2.234	2.299	

5 特性图

Pressure drop in cooling circuit (typical), Package

$\Delta p = f(\Delta V/\Delta t)$

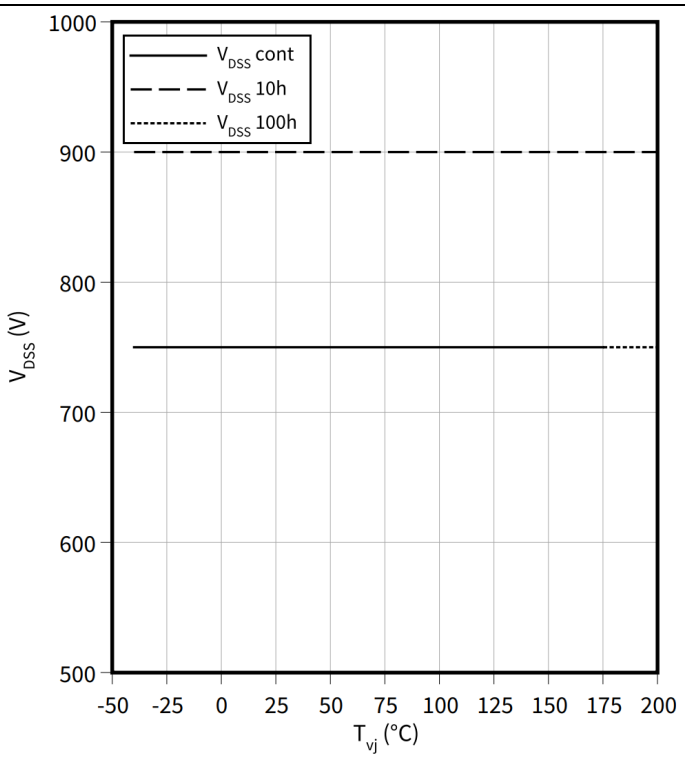
T_f = 60 °C, 50% water / 50% ethylene glycol



Maximum allowed drain-source voltage, MOSFET

$V_{DSS} = f(T_{vj})$

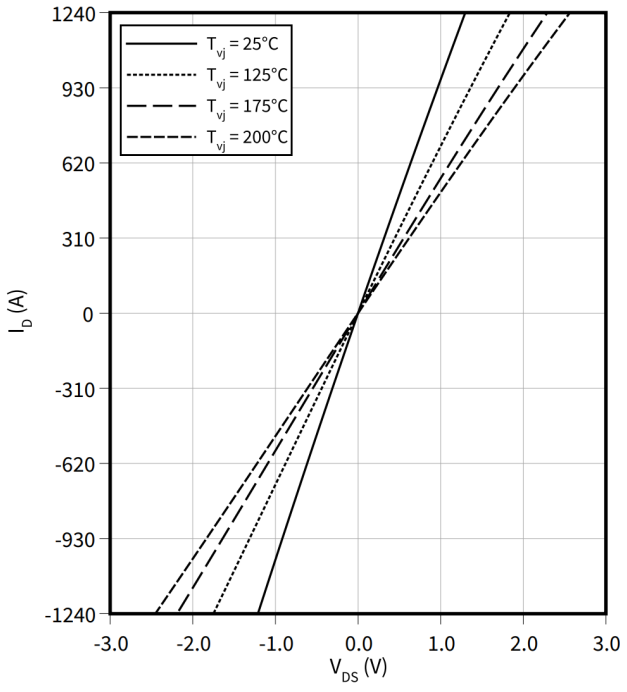
Verified by characterization / design, not by test



Output characteristic (typical), MOSFET

$I_D = f(V_{DS})$

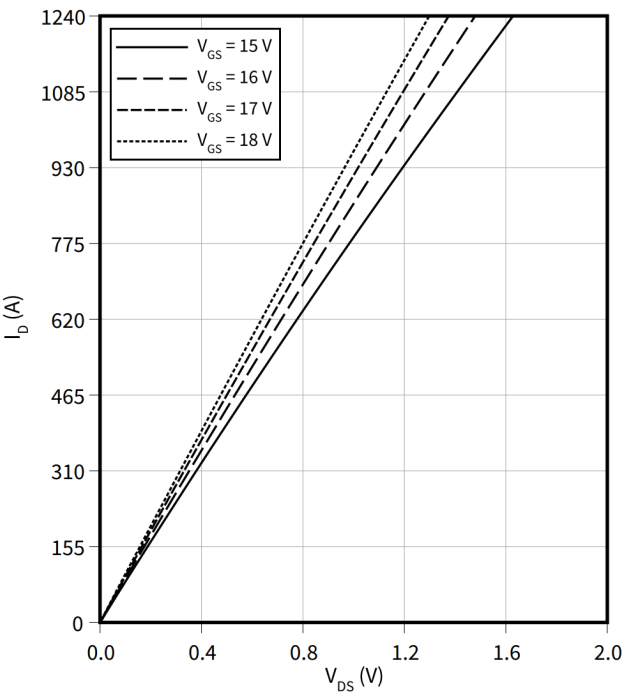
V_{GS} = 18 V



Output characteristic (typical), MOSFET

$I_D = f(V_{DS})$

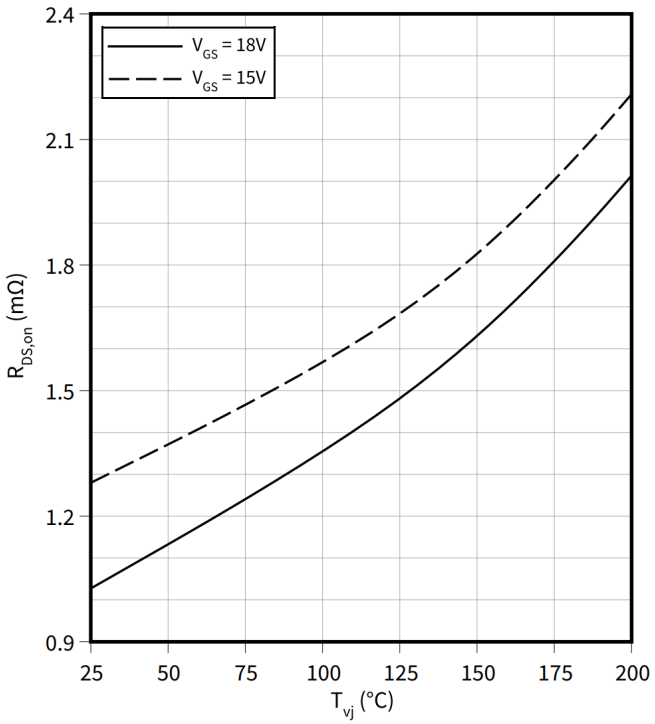
T_{vj} = 25 °C



Drain-source on-resistance (typical), MOSFET

$R_{DS,on} = f(T_{vj})$

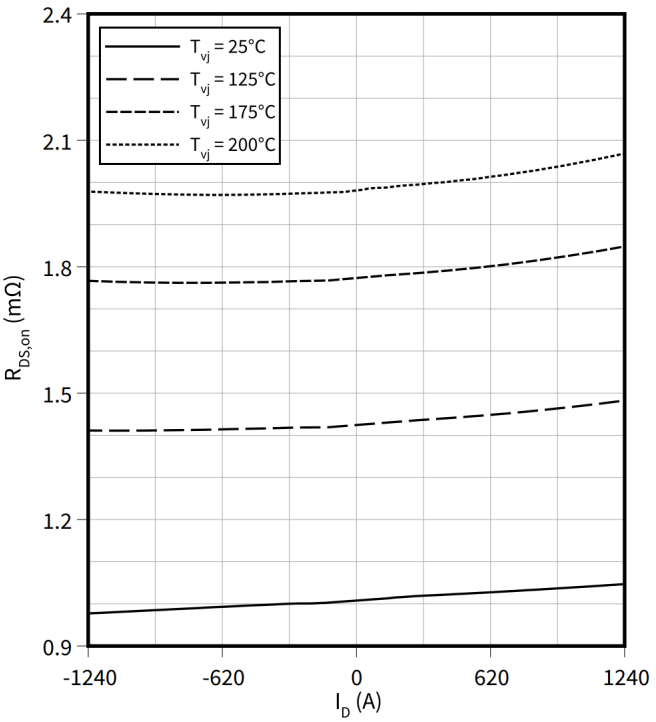
$I_D = 620$ A



Drain-source on-resistance (typical), MOSFET

$R_{DS,on} = f(I_D)$

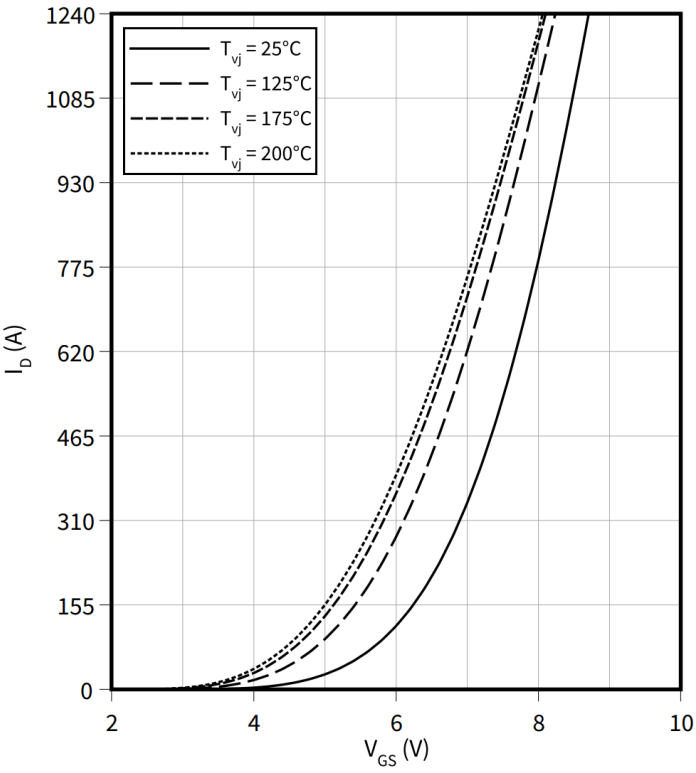
$V_{GS} = 18$ V



Transfer characteristic (typical), MOSFET

$I_D = f(V_{GS})$

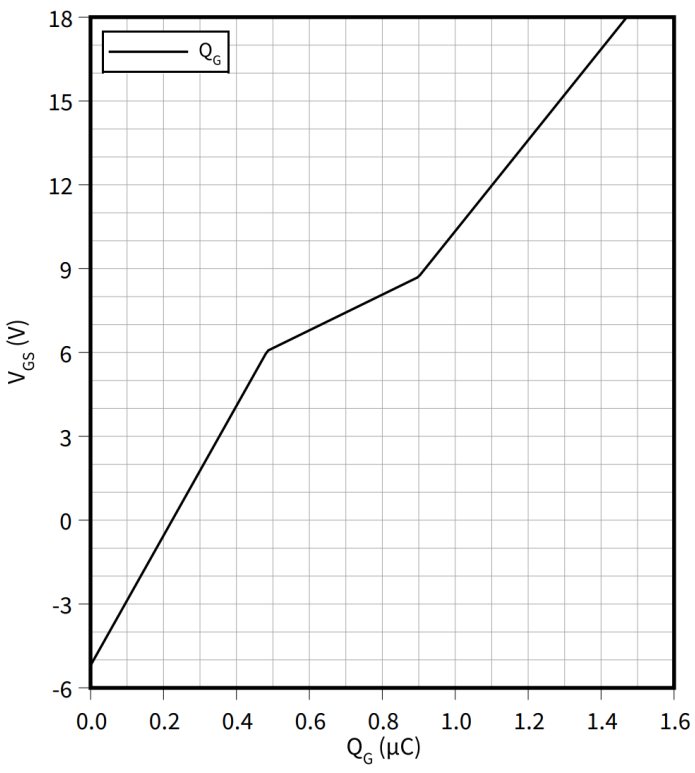
$V_{DS} = 20$ V



Gate charge characteristic (typical), MOSFET

$V_{GS} = f(Q_G)$

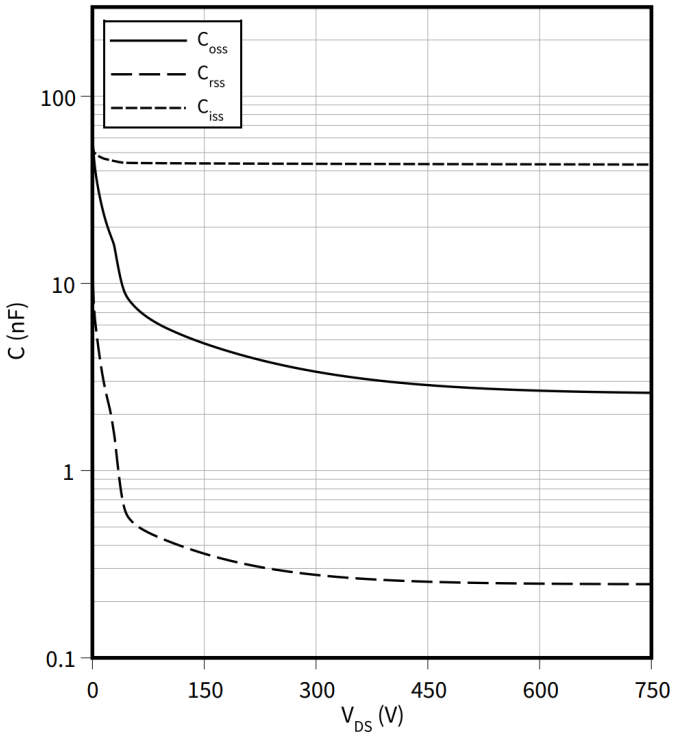
$V_{DD} = 470$ V, $T_{vj} = 25$ °C



Capacity characteristic (typical), MOSFET

$C = f(V_{DS})$

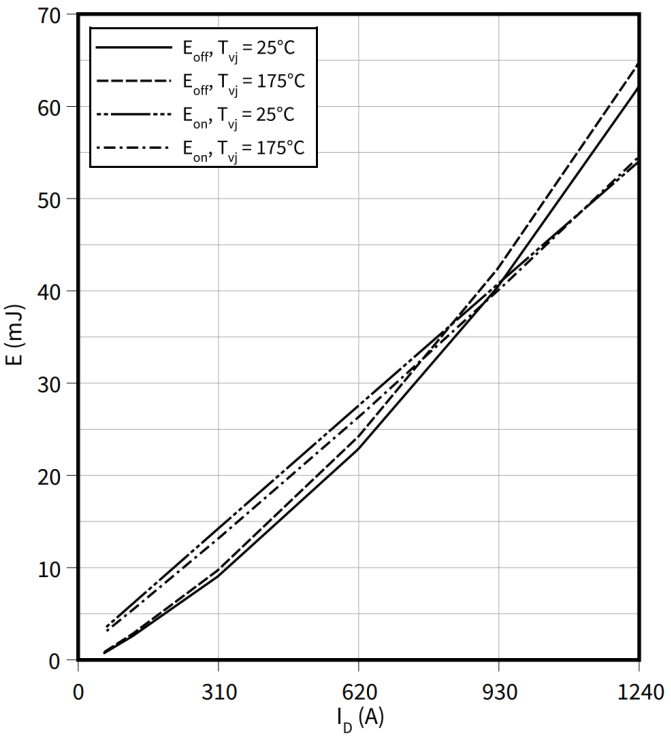
$f = 1$ MHz, $V_{GS} = -5/18$ V, $T_{vj} = 25$ °C



Switching losses (typical), MOSFET

$E = f(I_D)$

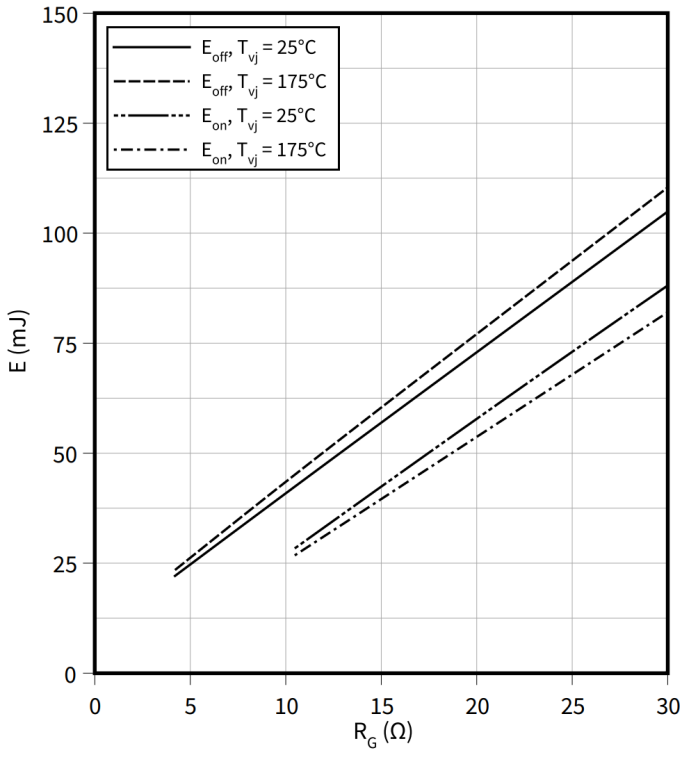
$V_{DS} = 470$ V, $R_{G,off} = 4.2\ \Omega$, $R_{G,on} = 10.5\ \Omega$, $V_{GS} = -5/18$ V



Switching losses (typical), MOSFET

$E = f(R_G)$

$I_D = 620$ A, $V_{DS} = 470$ V, $V_{GS} = -5/18$ V

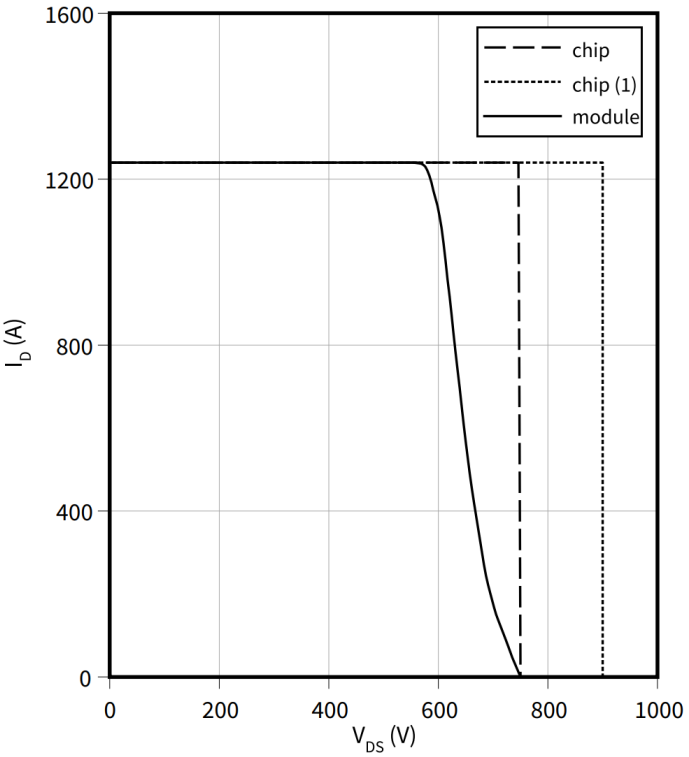


Reverse bias safe operating area (RBSOA), MOSFET

$I_D = f(V_{DS})$

$R_{G,off} = 4.2\ \Omega$, $V_{GS} = +18/-5$ V, $T_{vj} = 175$ °C

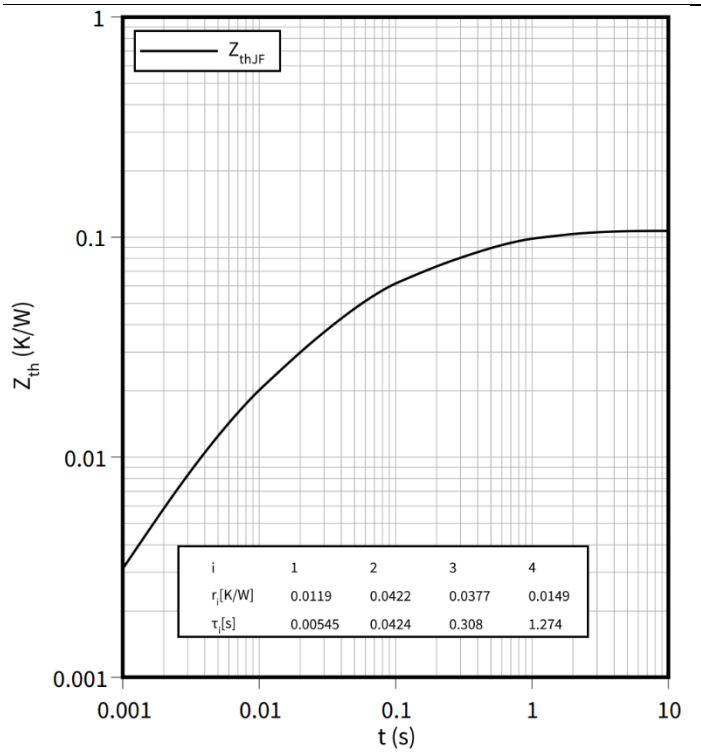
(1) for 10h over lifetime



Transient thermal impedance (typical), MOSFET

$Z_{th} = f(t)$

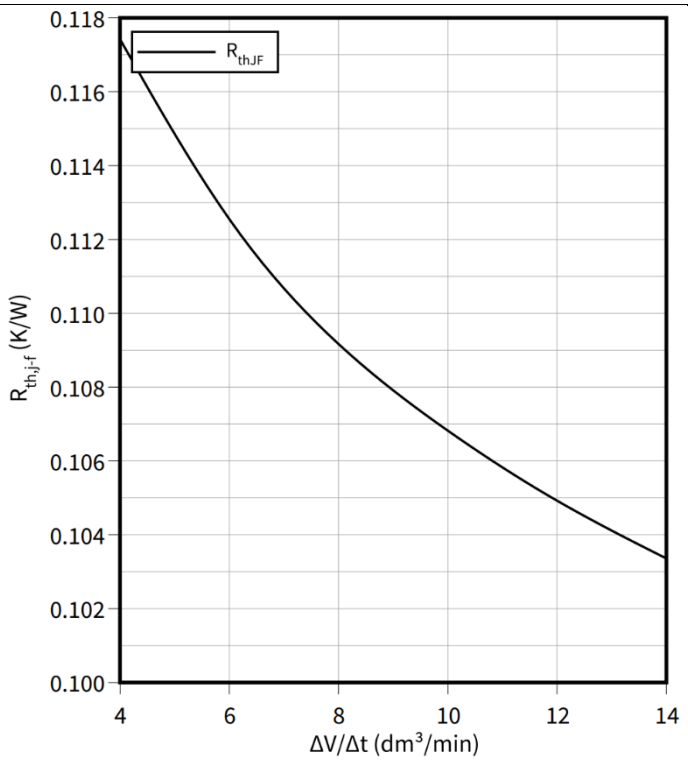
$\Delta V/\Delta t$ = 10 dm³/min, 50% water / 50% ethylene glycol , T_f = 60 °C



Thermal impedance (typical), MOSFET

$R_{th,j\text{-}f} = f(\Delta V/\Delta t)$

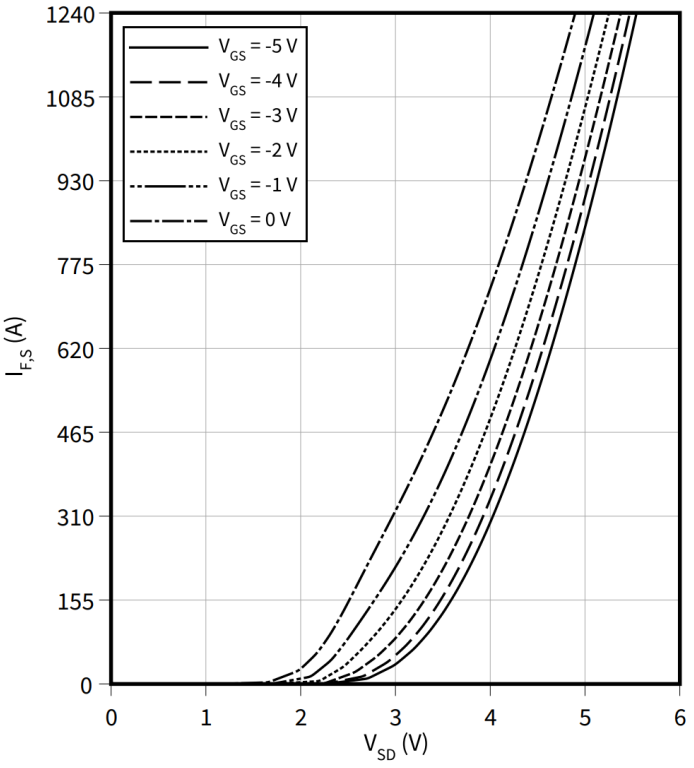
50% water / 50% ethylene glycol , T_f = 60 °C



Forward characteristic body diode (typical), MOSFET

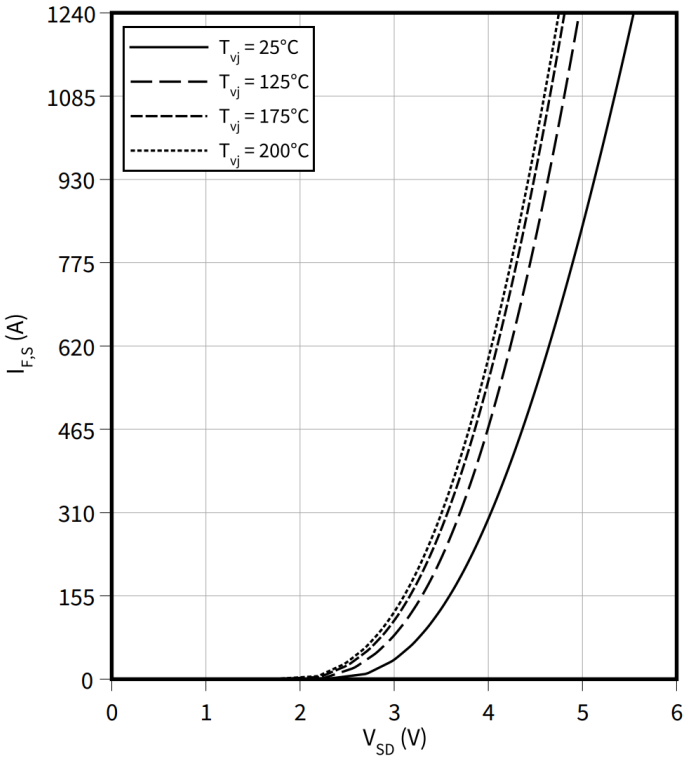
$I_{F,S} = f(V_{SD})$

T_{vj} = 25 °C



Forward characteristic body diode (typical), MOSFET

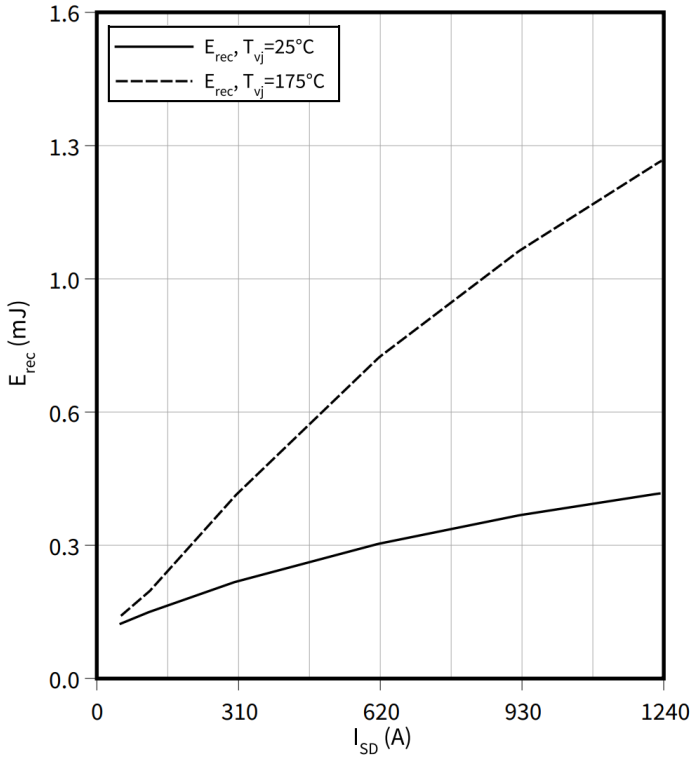
$I_{F,S} = f(V_{SD})$ V_{GS} = -5 V



Switching losses body diode (typical), MOSFET

$E_{rec} = f(I_{SD})$

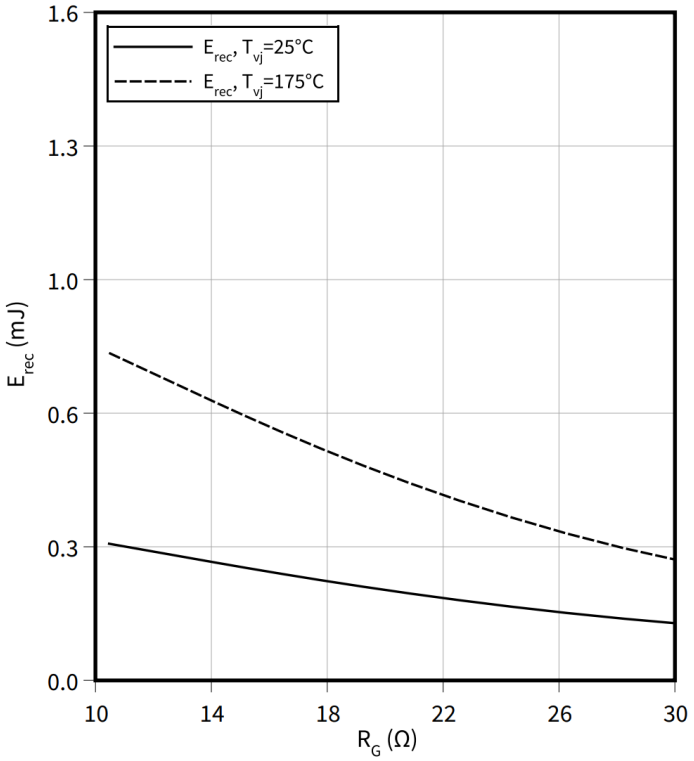
$R_{G,on} = 10.5\ \Omega$, $V_{R,DS} = 470\ V$



Switching losses body diode (typical), MOSFET

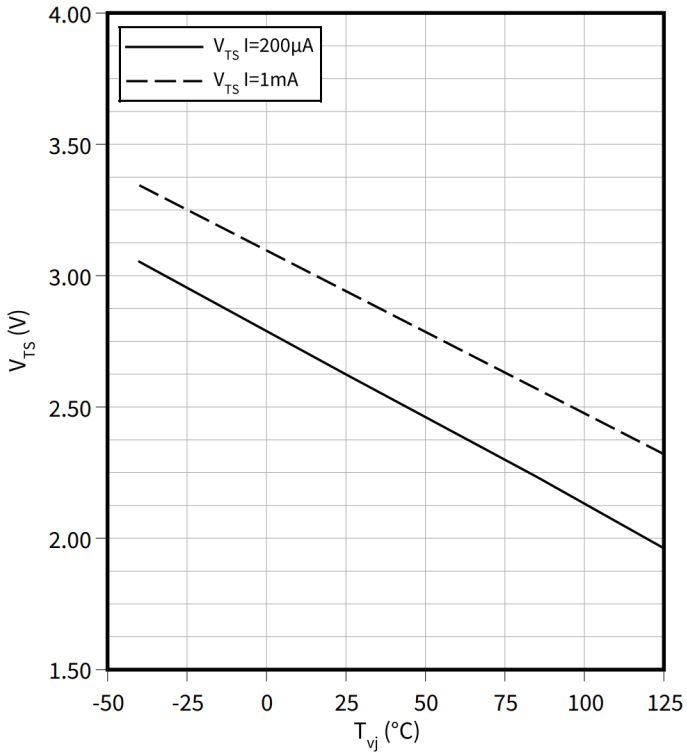
$E_{rec} = f(R_G)$

$I_{F,S} = 620\ A$, $V_{R,DS} = 470\ V$



Temperature characteristic (typical), Temperature sensor

$V_{TS} = f(T_{vj})$



6 电路图

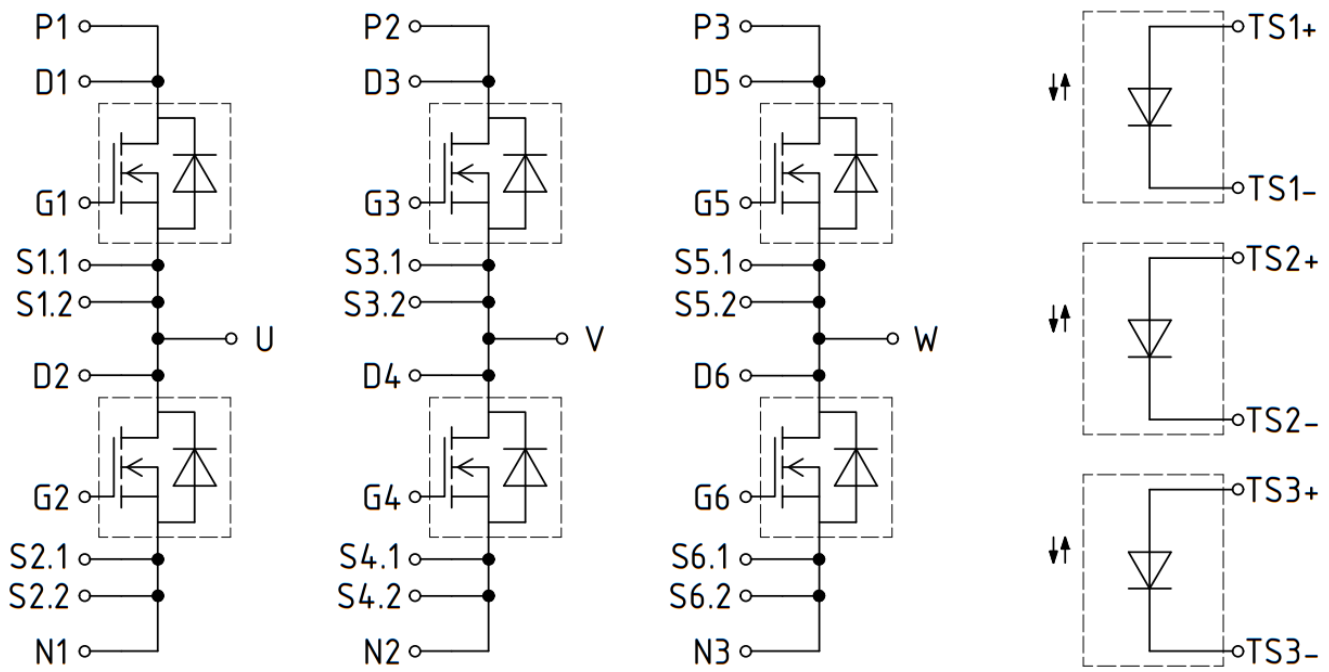

P1
D1
G1
S1.1
S1.2
U
D2
G2
S2.1
S2.2
N1
P2
D3
G3
S3.1
S3.2
V
D4
G4
S4.1
S4.2
N2
P3
D5
G5
S5.1
S5.2
W
D6
G6
S6.1
S6.2
N3
TS1+
TS1-
TS2+
TS2-
TS3+
TS3-

图 1

7 封装外形

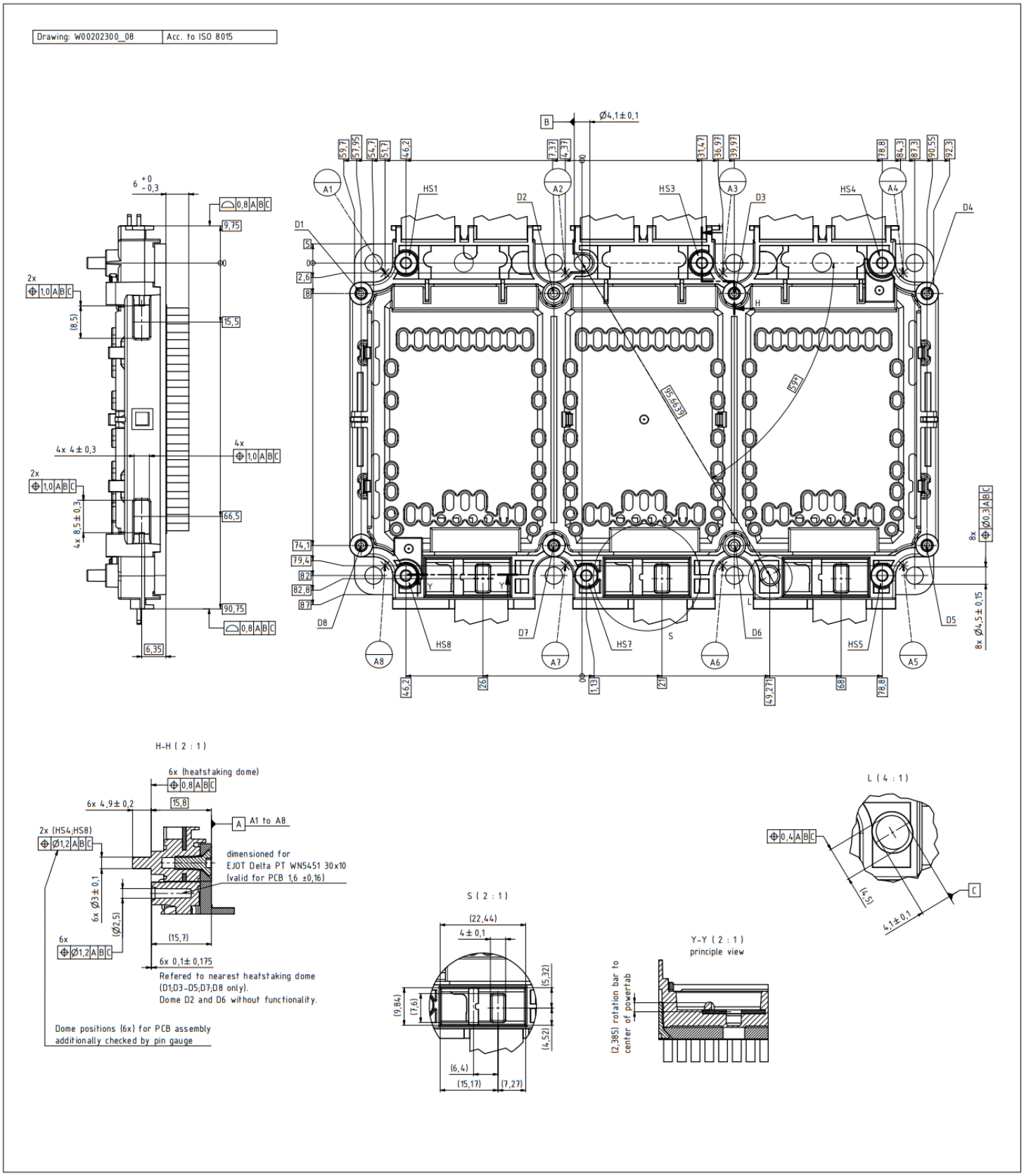

Drawing: W00202300_08
Acc. to ISO 8015
H-H (2 : 1)
S (2 : 1)
Y-Y (2 : 1)
principle view
L (4 : 1)
6x (heatstaking dome)
A1 to A8
dimensioned for
EJOT Delta PT WN5451 30x10
(valid for PCB 1,6 ±0,16)
Refered to nearest heatstaking dome
(D1;D3-D5;D7;D8 only).
Dome D2 and D6 without functionality.
Dome positions (6x) for PCB assembly
additionally checked by pin gauge
(2,385) rotation bar to
center of powertab

图 2

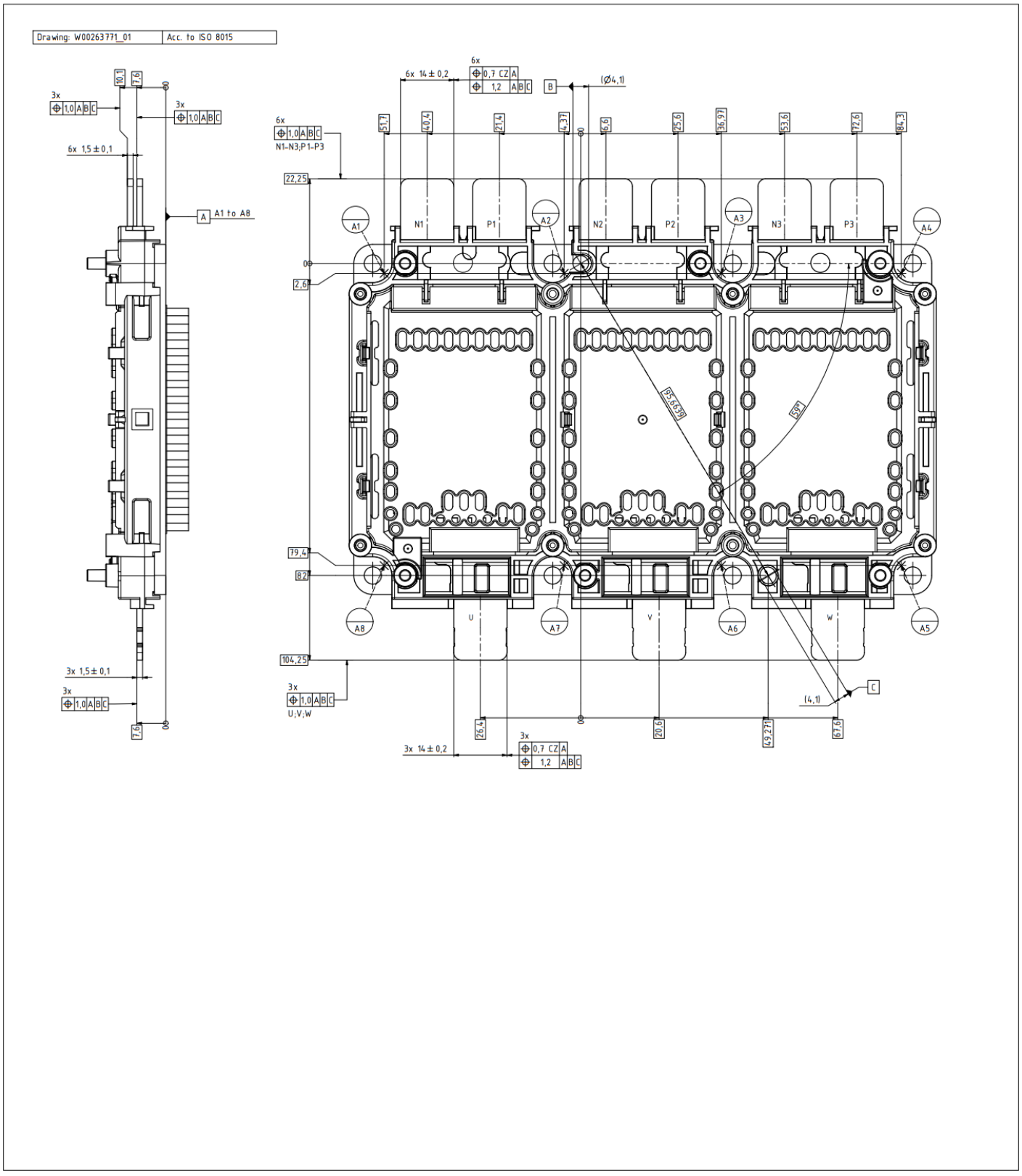

Drawing: W00263771_01
Acc. to ISO 8015
A1 to A8
N1–N3;P1–P3
U;V;W
N1
P1
N2
P2
N3
P3
A1
A2
A3
A4
A5
A6
A7
A8
U
V
W
R5,6639
59°
(Ø4,1)
(4,1)

图 3

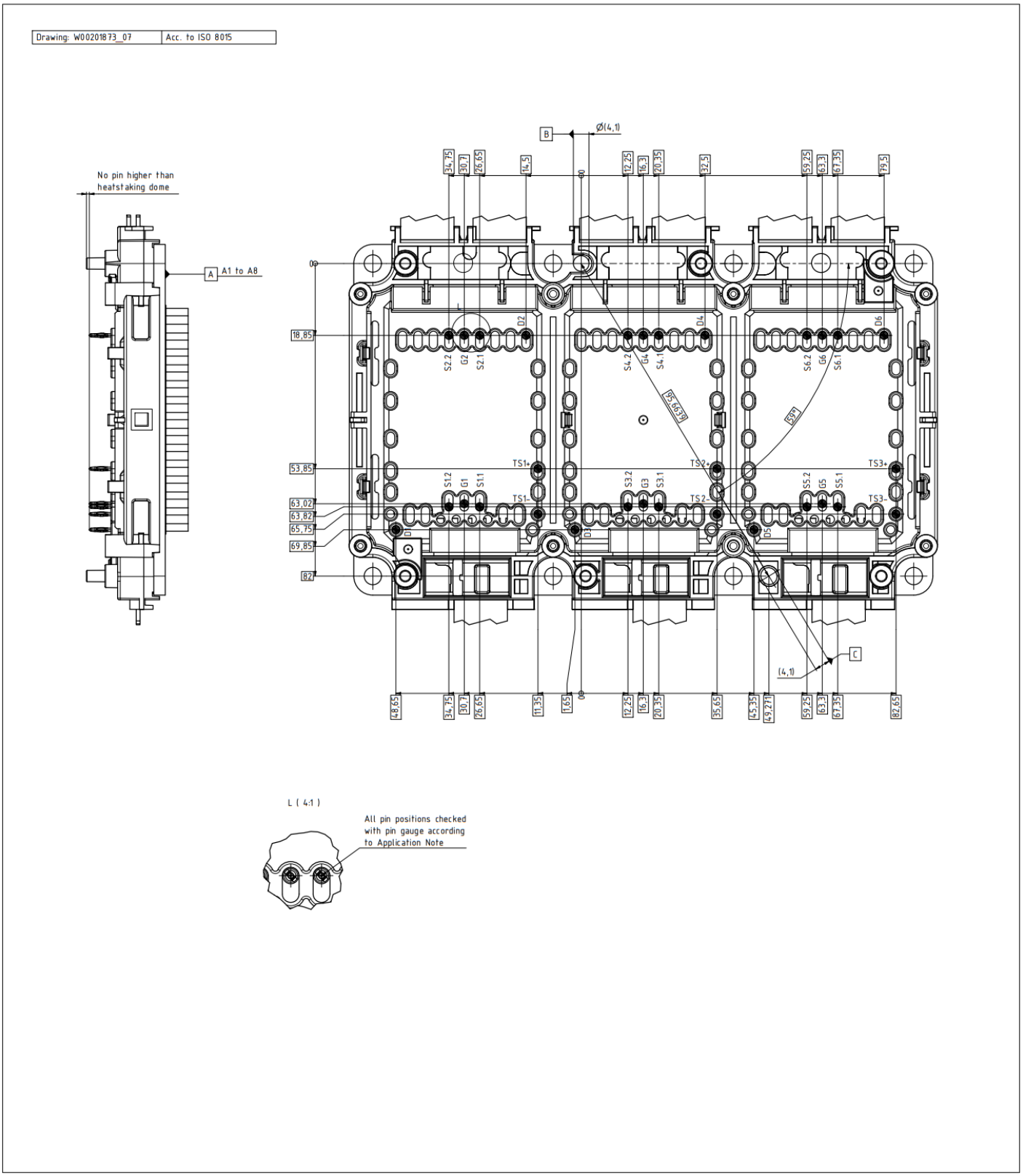

Drawing: W00201873_07
Acc. to ISO 8015
No pin higher than heatstaking dome
A
A1 to A8
B
Ø(4,1)
C
(4,1)
L (4:1)
All pin positions checked with pin gauge according to Application Note
TS1+
TS1-
TS2+
TS2-
TS3+
TS3-

图 4

8 模块标签代码

模块标签代码

Code format	Data Matrix	Barcode Code128
Encoding	ASCII text	Code Set A
Symbol size	16x16	23 digits
Standard	IEC24720 and IEC16022	IEC8859-1

Code content	*Content*	*Digit*	*Example*
	Module serial number	1 – 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 – 21	15
	Date code (production week)	22 – 23	30

Example



7154914284655054991530 7154914284655054991530

包装标签代码

Code format	Barcode Code128
Encoding	Code Set A
Symbol size	34 digits
Standard	IEC8859-1

Code content	*Content*	*Identifier*	*Digit*	*Example*
	Backend Construction Number	X	2 – 9	95056609
	Production Lot Number	1T	12 – 19	2X0003E0
	Serial Number	S	21 – 25	754389
	Date code	9D	28 – 31	1139
	Box Quantity	Q	33 – 34	15

Example



X950566091T2X0003E0S754389D1139Q15

图 5

修订记录

Document revision	Date of release	Description of changes
0.10	2024-10-29	Preliminary datasheet
1.00	2025-07-08	Final datasheet

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